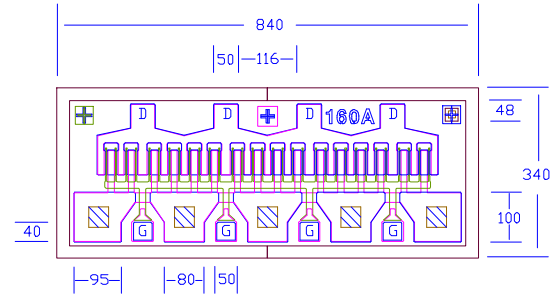


DATA SHEET
High Efficiency Heterojunction Power FET

- +31.0dBm TYPICAL OUTPUT POWER
- 8.5dB TYPICAL POWER GAIN FOR EPA160A AND 10.0dB FOR EPA160AV AT 18GHz
- 0.3 X 1600 MICRON RECESSED "MUSHROOM" GATE
- Si₃N₄ PASSIVATION
- ADVANCED EPITAXIAL DOPING PROFILE PROVIDES HIGH POWER EFFICIENCY, LINEARITY AND RELIABILITY
- EPA160AV WITH VIA HOLE SOURCE GROUNDING
- Idss SORTED IN 40mA PER BIN RANGE



Chip Thickness: 75 ± 20 microns

All Dimensions In Microns

⊞ : Via Hole

No Via Hole For EPA160A

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

SYMBOLS	PARAMETERS/TEST CONDITIONS	EPA160A			EPA160AV			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
P_{1dB}	Output Power at 1dB Compression f=12GHz	29.0	31.0		29.0	31.0		dBm
	V _{ds} =8V, I _{ds} =50% I _{dss} f=18GHz		31.0			31.0		
G_{1dB}	Gain at 1dB Compression f=12GHz	9.5	11.5		10.0	12.0		dB
	V _{ds} =8V, I _{ds} =50% I _{dss} f=18GHz		8.5			10.0		
PAE	Gain at 1dB Compression V _{ds} =8V, I _{ds} =50% I _{dss} f=12GHz		45			46		%
I_{dss}	Saturated Drain Current V _{ds} =3V, V _{gs} =0V	290	480	660	290	480	660	mA
G_m	Transconductance V _{ds} =3V, V _{gs} =0V	320	500		320	500		mS
V_p	Pinch-off Voltage V _{ds} =3V, I _{ds} =4.5mA		-1.0	-2.5		-1.0	-2.5	V
BV_{gd}	Drain Breakdown Voltage I _{gd} =1.6mA	-11	-15		-11	-15		V
BV_{gs}	Source Breakdown Voltage I _{gs} =1.6mA	-7	-14		-7	-14		V
R_{th}	Thermal Resistance (Au-Sn Eutectic Attach)		30			22		°C/W

MAXIMUM RATINGS AT 25°C

SYMBOLS	PARAMETERS	EPA160A		EPA160AV	
		ABSOLUTE ¹	CONTINUOUS ²	ABSOLUTE ¹	CONTINUOUS ²
V_{ds}	Drain-Source Voltage	12V	8V	12V	8V
V_{gs}	Gate-Source Voltage	-8V	-3V	-8V	-3V
I_{ds}	Drain Current	I _{dss}	475mA	I _{dss}	625mA
I_{gsf}	Forward Gate Current	80mA	14mA	80mA	14mA
P_{in}	Input Power	28dBm	@ 3dB Compression	28dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175°C	150°C	175°C	150°C
T_{stg}	Storage Temperature	-65/175°C	-65/150°C	-65/175°C	-65/150°C
P_t	Total Power Dissipation	4.5W	3.8W	6.0W	5.0W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

Excelics Semiconductor, Inc., 2908 Scott Blvd., Santa Clara, CA 95054

Phone: (408) 970-8664 Fax: (408) 970-8998 Web Site: www.excelics.com

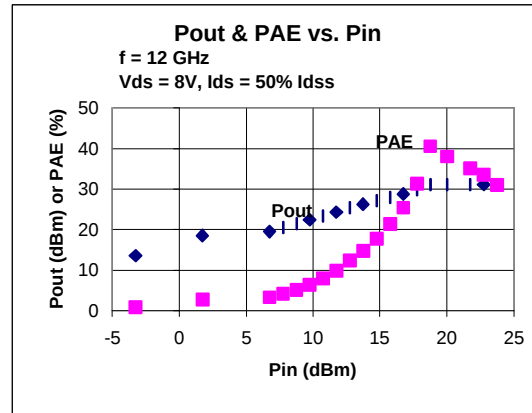
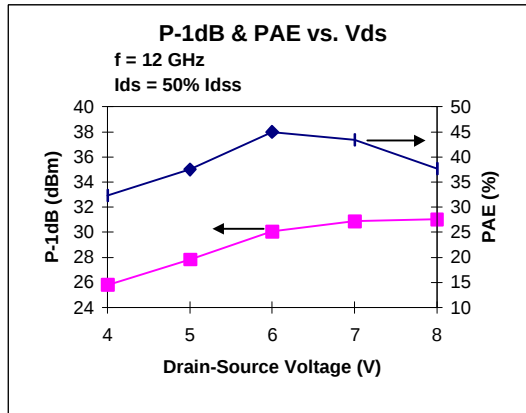
EPA160A/EPA160AV

DATA SHEET

www.DataSheet4U.com

High Efficiency Heterojunction Power FET

EPA160A



S-PARAMETERS

EPA160A 8V, 1/2 Idss

FREQ (GHz)	S11 MAG	S11 ANG	S21 MAG	S21 ANG	S12 MAG	S12 ANG	S22 MAG	S22 ANG
1.0	0.915	-119.9	14.906	114.4	0.027	31.0	0.302	-128.9
2.0	0.907	-149.2	8.322	96.0	0.029	19.1	0.331	-146.1
4.0	0.907	-168.1	4.370	77.6	0.031	14.5	0.362	-151.0
6.0	0.908	-180.0	2.898	63.8	0.030	14.2	0.411	-150.0
8.0	0.912	-174.7	2.172	52.5	0.030	16.0	0.448	-152.1
10.0	0.918	-170.0	1.693	41.7	0.028	17.0	0.498	-155.7
12.0	0.923	-165.9	1.349	31.4	0.028	21.7	0.549	-160.3
14.0	0.931	-162.9	1.084	22.4	0.028	23.4	0.601	-162.8
16.0	0.936	-160.3	0.896	13.7	0.028	25.0	0.658	-166.7
18.0	0.941	-159.3	0.761	5.9	0.029	25.3	0.697	-170.4
20.0	0.936	-158.5	0.675	-2.0	0.031	25.6	0.725	-175.6

FREQ (GHz)	S11 MAG	S11 ANG	S21 MAG	S21 ANG	S12 MAG	S12 ANG	S22 MAG	S22 ANG
21.0	0.932	-155.6	0.642	-5.2	0.035	25.7	0.744	-175.4
22.0	0.932	-150.8	0.601	-8.9	0.035	26.0	0.747	-174.5
24.0	0.932	-143.6	0.526	-16.4	0.040	27.1	0.778	-175.2
26.0	0.928	-139.3	0.460	-23.2	0.043	28.0	0.783	-179.1
28.0	0.917	-135.6	0.403	-31.9	0.049	25.7	0.820	-170.8
30.0	0.917	-133.4	0.350	-39.1	0.051	20.1	0.834	-164.0
32.0	0.912	-128.2	0.294	-46.1	0.048	19.9	0.865	-162.3
34.0	0.915	-123.6	0.255	-50.3	0.048	23.0	0.876	-163.9
36.0	0.942	-126.8	0.223	-52.3	0.048	22.2	0.869	-162.9
38.0	0.957	-129.8	0.212	-53.8	0.055	17.0	0.872	-158.9
40.0	0.952	-138.3	0.205	-60.1	0.055	4.9	0.843	-147.4

EPA160AV 8V, 1/2 Idss

FREQ (GHz)	S11 MAG	S11 ANG	S21 MAG	S21 ANG	S12 MAG	S12 ANG	S22 MAG	S22 ANG
1.0	0.922	-115.7	13.969	116.1	0.027	30.9	0.271	-114.5
2.0	0.914	-146.8	7.872	96.1	0.031	17.2	0.299	-134.2
4.0	0.917	-165.9	4.057	76.9	0.030	7.9	0.341	-140.5
6.0	0.923	-176.7	2.690	63.0	0.029	4.3	0.393	-140.1
8.0	0.929	-177.6	2.027	51.5	0.027	4.6	0.430	-148.0
10.0	0.930	-178.2	1.596	40.1	0.025	4.2	0.485	-157.8
12.0	0.936	-175.2	1.273	28.3	0.023	1.8	0.556	-161.5
14.0	0.941	-171.3	1.025	17.7	0.021	1.5	0.626	-167.2
16.0	0.950	-167.4	0.833	8.1	0.021	2.2	0.688	-170.1
18.0	0.953	-168.3	0.695	0.3	0.022	3.2	0.732	-176.3
20.0	0.955	-165.1	0.597	-7.2	0.022	3.0	0.768	-177.8

FREQ (GHz)	S11 MAG	S11 ANG	S21 MAG	S21 ANG	S12 MAG	S12 ANG	S22 MAG	S22 ANG
21.0	0.957	-163.3	0.582	-11.9	0.023	5.0	0.766	-179.4
22.0	0.956	-162.5	0.536	-15.4	0.024	4.2	0.786	-179.1
24.0	0.954	-159.0	0.452	-22.5	0.024	8.6	0.821	-176.3
26.0	0.953	-158.6	0.384	-30.1	0.026	10.9	0.844	-169.1
28.0	0.932	-153.0	0.335	-37.8	0.026	11.9	0.880	-165.4
30.0	0.918	-146.4	0.295	-46.5	0.028	9.1	0.899	-161.7
32.0	0.877	-145.0	0.262	-56.0	0.027	-0.3	0.949	-153.2
34.0	0.934	-144.2	0.229	-63.9	0.024	-3.7	0.896	-146.3
36.0	0.968	-144.4	0.214	-69.5	0.025	-6.0	0.916	-141.6
38.0	0.985	-146.4	0.201	-74.3	0.028	-22.8	0.952	-137.4
40.0	0.986	-146.4	0.189	-77.5	0.035	-40.3	0.952	-137.2

Note: The data included 0.7 mils diameter Au bonding wires; 3 gate wires, 15 mils each; 3 drain wires, 20 mils each; 10 source wires, 7 mils each; no source wires for EPA160AV.